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PRESIDENCY UNIVERSITY **BENGALURU**

SCHOOL OF ENGINEERING

MAKE UP EXAMINATION – JAN 2023

Course Code: ECE 2001

Course Name: Analog Electronics

Program & Sem: B. Tech (ECE)

Date: 23-JAN-2023

Time: 9.30 to 12.30 PM

Max Marks: 60

Weightage: 30 %

Instructions:

(i) Read the all questions carefully and answer accordingly.

Part A [Memory Recall Questions]

Answer all the Questions. Each question carries TWO mark.

(10Qx 2M = 20M)

- 1. BJTs can be connected in different configuration, Name any two configurations for a BJT. (C.O.No.2) [Knowledge] 2. For a MOSFET define the term threshold voltage (C.O.No.3) [Knowledge] 3. BJTs are bipolar junction transistors used in switching and amplification. In a BJT the circuit is reverse biased circuit is forward biased (C.O.No.2) [Knowledge] 4. Pure semiconductors are also called as _____ semiconductors. Doped semiconductors are also called as semiconductors. (C.O.No.1) [Knowledge] 5. Stabilization is done to keep the Q point stable. Stability of a circuit is depended on the value of S. If the value of S is larger the circuit stability is _____ (High/Low) (C.O.No.2) [Comprehension] 6. The circuit which shifts the DC level of any signal is called as _____ circuit. (C.O.No.2) [Knowledge] 7. Which is the rectifiers which has the least ripple? What is the value of the ripple? (C.O.No.2) [Knowledge]
- 8. For an n-channel JFET, calculate the value of resistance between the drain and the source if

 $I_D = 10nA$, $I_{DSS} = 100nA$, $V_{GS} = 8V$.

(C.O.No.3) [Knowledge]

9. Choose the correct option.

JFET can be damaged, if not operated with proper voltages. Which of the following could be a reason for the JFET to be damaged

a.
$$V_{GS} = 0$$
; $V_{DS} = positive$

b. V_{GS} <0; V_{DS} = positive

c.
$$V_{GS} > 0$$
; $V_{DS} = positive$

10 0 :		,					A '11 4	
10. Osci		t and a	_	rate repetitive _circuit	e periodic	signals.		consists of an [Comprehension]
Part B [Thought Provoking Questions]								
Answer a	all the Que	estions. Ea	ch questio	n carries FIVE	E marks.	(4	Qx5M=20M)	
				ession for IB. I 00. Draw the c				of S of the Comprehension]
	and explai semicondu		on law. Diff	erentiate betw	een direct	bandgap		ors and indirect 1) [Knowledge]
13. Powe amplifiers	-	raises the p	oower level	of the signal.	Power amp	olifier is al	so called larg	e signal
	•	and power	•	having largest hich gives a s	•		Can you name	e this power
C.	Draw the	e circuit iden	itified in par	t b of this ques	stion and e	explain its	•	Comprehension]
and the o operation 15. Feedl part or fra a. b.	utput chara back Ampli action of ou If the feedl Draw a blo determine	fier is a devote the compact of the compact is added to the compact of the compact of the compact of the express	or the MOSF vice that is be bined with the ed back to in representa sion for gain	FET. Different	rinciple of town as feed e amplifier cuit in part	en depleti feedback. dback. is named a of the c	on and enhand (C.O.No. 3) of The process as a squestion and camplifiers	r. Sketch its input cement modes of [Comprehension] by which some
			Part C [Problem Solv	ing Quest	tions]		
Answer a	all the Que	estions. Ea	ch questio	n carries TEN	l marks.	(20	Qx10M=20M)	
	•		•	having Ri = 7 back is 3%. Th		-		is Ro series with the
a.	Determir Let the d	ne the input istortion of	and output the circuit w	iplifier and det resistance wit ith feedback b thout feedbac	h feedback oe 2, What	is the dist	tortion without	feedback? h with feedback?
						[10] (C.O.No.4) [Co	mprehension]
			istors and p mA, Vp = -4	=	se of their s	size, powe	er consumptio	n and speed. For

- a. For VGS = -2V. Determine the value of Id,
- b. Find rd if ro = $1K\Omega$
- c. Find the amplification factor
- d. Draw the drain and transfer characteristics

[10] (C.O.No.4) [Comprehension]